

SILICON EPITAXIAL PLANAR TYPE  
VARIABLE CAPACITANCE DIODE

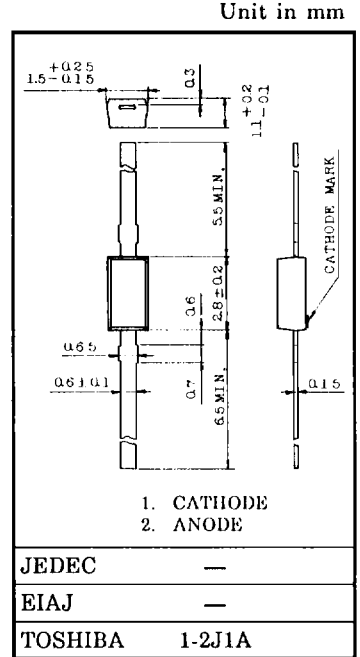
# 1SV212

VCO FOR UHF BAND RADIO

- Ultra Low Series Resistance:  $r_s = 0.2\Omega$  (Typ.)
- Useful for Small Size Set

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

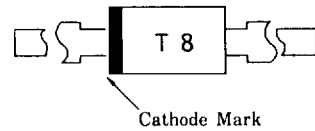
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$V_R$	15	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ\text{C}$

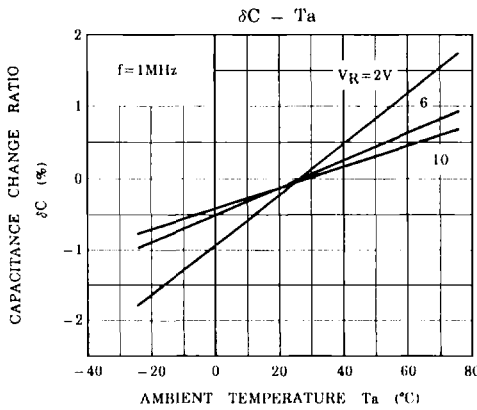
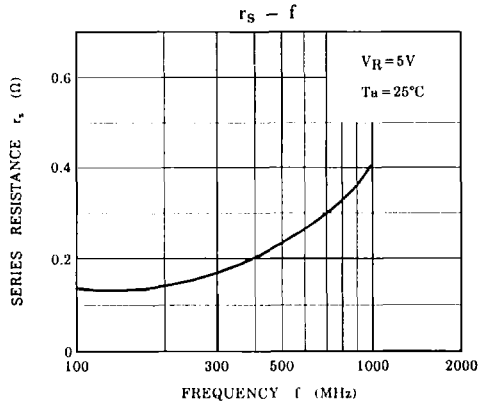
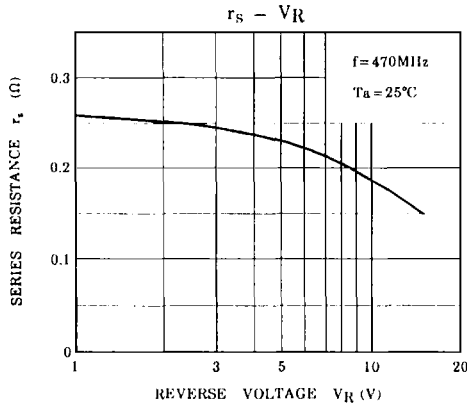
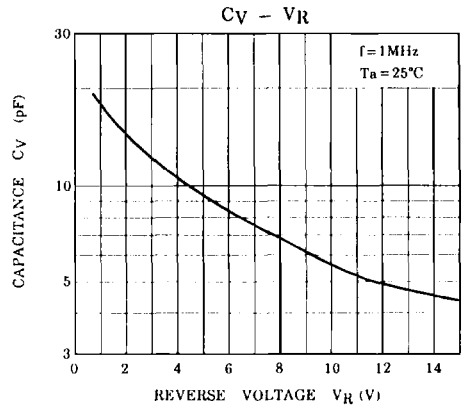
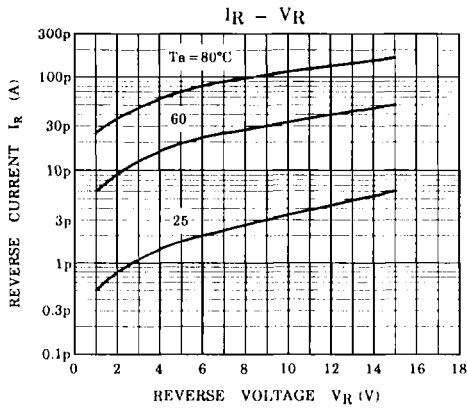


ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	$V_R$	$I_R = 1\mu\text{A}$	15	—	—	V
Reverse Current	$I_R$	$V_R = 15\text{V}$	—	—	3	nA
Capacitance	C2V	$V_R = 2\text{V}, f = 1\text{MHz}$	14	15	16	pF
Capacitance	C10V	$V_R = 10\text{V}, f = 1\text{MHz}$	5.5	6	6.5	pF
Capacitance Ratio	C2V / C10V	—	2.0	2.5	—	—
Series Resistance	$r_s$	$V_R = 5\text{V}, f = 470\text{MHz}$	—	0.2	0.4	$\Omega$

Marking





NOTE : 
$$\Delta C (\%) = \frac{C(T_a) - C(25^\circ\text{C})}{C(25^\circ\text{C})} \times 100$$